

## **NPN General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100A for characteristics.

#### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>CES</sub>	Collector-Base Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		BC548 / A / B / C	
Pp	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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# NPN General Purpose Amplifier

Symbol	Parameter	Test Conditions	Min	Max	Units
	RACTERISTICS	1		1	1
/ <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	30		V
(BR)CBO	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$	30		V
/ <sub>(BR)CES</sub>	Collector-Base Breakdown Voltage	$I_{C} = 10 \ \mu A, \ I_{E} = 0$	30		V
/ <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, \ I_{C} = 0$	5.0		V
СВО	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$ $V_{CB} = 30 \text{ V}, I_E = 0, T_A = +150 \text{ °C}$		15 5.0	nA μA
ON CHAR	ACTERISTICS				
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_C = 2.0 \text{ mA}$ 548	110	800	
		548A 548B	110 200	220 450	
		548C	420	800	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		0.25	V
N/	Base-Emitter On Voltage	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$ $V_{\rm CE} = 5.0 \text{ V}, I_{\rm C} = 2.0 \text{ mA}$	0.58	0.60 0.70	V V
V <sub>BE(on)</sub>	Base-Emilier On Vollage	$V_{CE} = 5.0 \text{ V}, I_C = 2.0 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$	0.56	0.70	v
SMALL S <sup>h</sup> fe NF	IGNAL CHARACTERISTICS Small-Signal Current Gain Noise Figure	$\label{eq:lc} \begin{array}{l} I_{C} = 2.0 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ f = 1.0 \text{ kHz} \\ V_{CE} = 5.0 \text{ V}, \ I_{C} = 200 \ \mu\text{A}, \end{array}$	125	900 10	dB
		$ \begin{array}{l} R_{S} = 2.0 \; k\Omega, \; f = 1.0 \; kHz, \\ B_{W} = 200 \; Hz \end{array} $			

BC548 / BC548A / BC548B / BC548C

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